

P-Channel 150-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)	
- 150	0.635 at V _{GS} = - 10 V	- 1.1	7.7	
	0.890 at V _{GS} = - 4.5 V	- 0.7	7.7	

FEATURES

• TrenchFET Power MOSFET



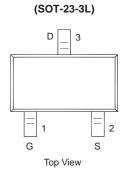
100% R_g and UIS Tested

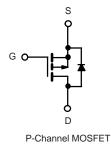


ROHS

APPLICATIONS

• Active Clamp Circuits in DC/DC Power Supplies





ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise n	oted		
Parameter	Symbol	LIMIT			
Drain-Source Voltage		V_{DS}	- 150	V	
Gate-Source Voltage		V _{GS} ± 20		v	
Continuous Dunin Comment /T 150 °C\2 b	T _A = 25 °C	1	- 1.1		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C	l _D	- 0.75		
Pulsed Drain Current		I _{DM}	- 4.0	Α	
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 1.1		
Single Pulse Avalanche Current	L = 1.0 mH	I _{AS}	1.0		
Single Pulse Avalanche Energy	L = 1.0 IIII	E _{AS}	1.01	mJ	
Mariana Barra Birata ya a h	T _A = 25 °C	P _D	0.75	W	
Maximum Power Dissipation ^{a, b}	T _A = 70 °C	'D	0.48	vv	
Operating Junction and Storage Temperature Ran	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 5 s	B	75	100		
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	120	166	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	50]	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.



				Limits			
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			<u>'</u>	•			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = - 250 μA	- 150			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 2.0		- 4.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = - 120 V, V _{GS} = 0 V			- 1	μΑ	
	I _{DSS}	$V_{DS} = -120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -15 \text{ V}, V_{GS} = 10 \text{ V}$	- 1.1			Α	
		$V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$		635	795		
Drain-Source On-Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -0.5 \text{ A}$		890	1150	mΩ	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -15 \text{ V}, I_D = -0.5 \text{ A}$		2.2		S	
Diode Forward Voltage	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.7	- 1.2	٧	
Dynamic ^b							
Total Gate Charge	Q_g	V 100 V V 10 V		7.7	12		
Gate-Source Charge	Q_{gs}	$V_{DS} = -120 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} \cong -0.5 \text{ A}$		1.5		nC	
Gate-Drain Charge	Q _{gd}	ID = - 0.3 A		2.5			
Gate Resistance	R_g	f = 1.0 MHz		9		Ω	
Input Capacitance	C _{iss}			340	510		
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		30		pF	
Reverse Transfer Capacitance	C _{rss}			16			
Switching ^c							
Turn On Time	t _{d(on)}	V 400 V D 75 G		7	11		
Turn-On Time	$V_{DD} = -120 \text{ V, } R_L = 75 \Omega$ $I_D \cong -1.0 \text{ A, } V_{GEN} = -10 \text{ V}$		11	17	no		
Time Off Time	t _{d(off)}	$R_{\rm g} = 6 \Omega$		16	25	ns	
Turn-Off Time	t _f	g – 0 22		11	17		
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = 0.5 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		90	135	nC	

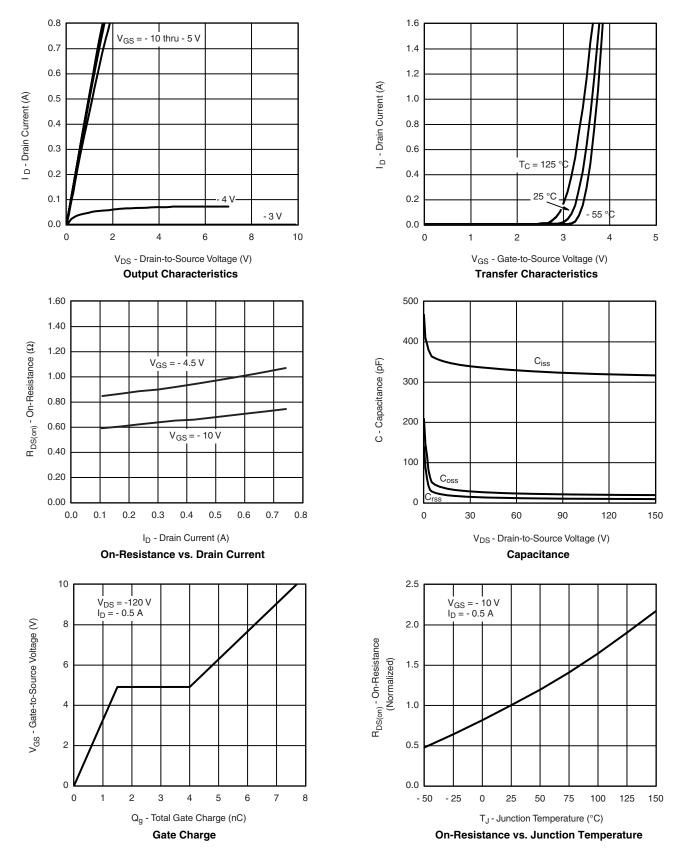
Notes:

- a. Pulse test: PW \leq 300 μs duty cycle \leq 2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

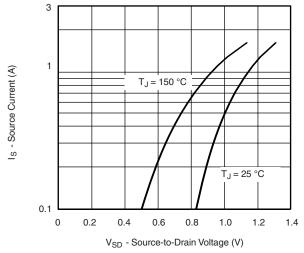


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

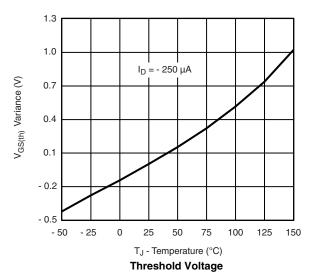


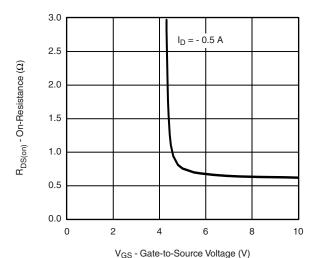


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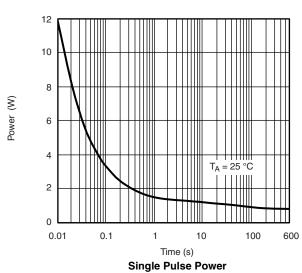


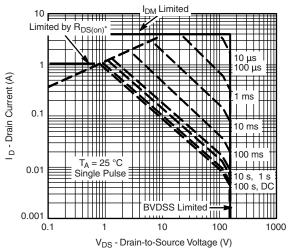
Source-Drain Diode Forward Voltage





On-Resistance vs. Gate-to-Source Voltage



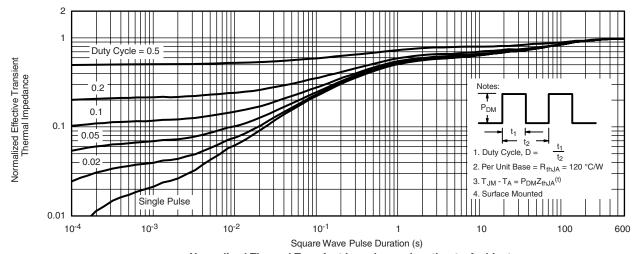


 v_{DS} - Drain-to-Source voltage (v) * v_{GS} > minimum v_{GS} at which $v_{DS(on)}$ is specified

Safe Operating Area



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

DIMENSIONS IN INCHES

NOM

0.039

MAX

0.049

0.005

0.045

0.020

0.008

0.122

0.118

0.071

0.024

8°

MIN

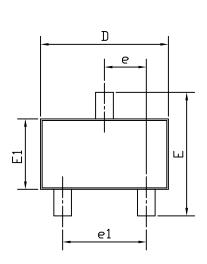
0.033

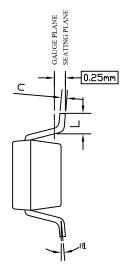
0.000

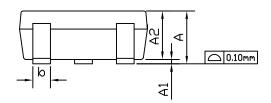
0.028



SOT-23-3L PACKAGE OUTLINE







SYMBOLS

A1

A2

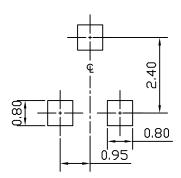
MIN

0.85

0.00

0.70

RECOMMENDED LAND PATTERN



0.30 0.40 0.50 0.012 0.016 b 0.08 0.13 0.20 0.003 0.005 2.80 2.90 D 3.10 0.110 0.114 2.80 Е 2.60 3.00 0.102 0.110 E1 1.60 1.80 0.055 0.063 1.40 0.95 BSC 0.037 BSC e 1.90 BSC 0.075 BSC e1 0.30 0.60 0.012 L θ1 0° 8° 0°

DIMENSIONS IN MILLIMETERS

NOM

1.00

MAX

1.25

0.13

1.15

UNIT: mm

NOTE

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS.
 MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
- 2. TOLERANCE ± 0.100 mm (4 mil) UNLESS OTHERWISE SPECIFIED.
- 3. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 5. ALL DIMENSIONS ARE IN MILLIMETERS.





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